

Product data sheet

## 1. General description

Ultrafast diode in a TO3PF package.

### 2. Features and benefits

- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET or IGBT

## 3. Applications

- Active PFC in air conditioner
- S.M.P.S Power Factor Correction (PFC)
- · Half-bridge / full-bridge switched-mode power supplies

## 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>h</sub> ≤ 73 °C; square-wave; Fig. 1; Fig. 2; Fig. 3	-	-	30	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; square-wave	-	-	60	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 4</u>	-	-	170	А
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN	-	-	190	А
Static chara	acteristics		· ·			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
Dynamic ch	haracteristics					
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A};  V_R = 30 \text{ V};  dI_F/dt = 100  \text{A}/\mu\text{s}; \\ T_j = 25 ^\circ\text{C};  \underline{\text{Fig. } 7}$	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/ \mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/ \mu s; T_j = 125 °C; Fig. 7$	-	138	-	ns

# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	А	anode		K – K – A
2	К	cathode		001aaa020
3	А	anode		
mb	n.c.	mounting base; isolated	TO3PF	

# 6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BYV30JT-600P	TO3PF	Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 3-lead TO-3P 'full pack'	TO3PF			

**Ultrafast recovery diode** 

## 7. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5; T <sub>h</sub> ≤ 73 °C; square-wave; <u>Fig. 1</u> ; Fig. 2; Fig. 3	-	30	A
I <sub>O(AV)</sub>	average output current	$\delta = 0.5$ ; $T_h \le 73$ °C; SQW	-	60	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; square-wave	-	60	A
I <sub>FSM</sub>	non-repetitive peak	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; SIN; <u>Fig. 4</u>	-	170	Α
	forward current	t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; SIN	-	190	А
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

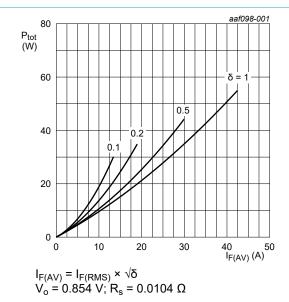
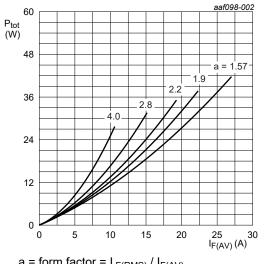


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; typical values



a = form factor = I  $_{F(RMS)}$  / I  $_{F(AV)}$  V  $_{o}$  = 0.854 V; R  $_{s}$  = 0.0104  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; typical values

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# **BYV30JT-600P**

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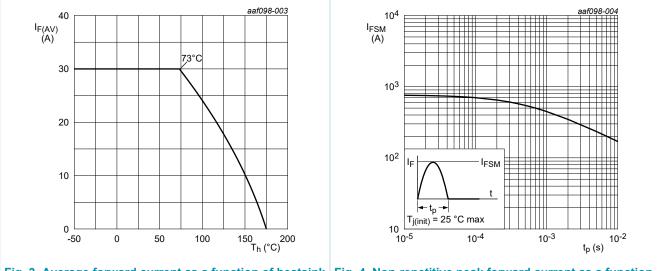
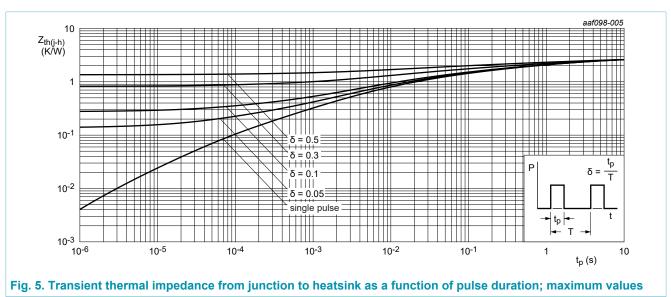


Fig. 3. Average forward current as a function of heatsink<br/>temperature; typical valuesFig. 4. Non-repetitive peak forward current as a function<br/>of pulse width; sinusoidal waveform; maximum values

Ultrafast recovery diode

#### 8. Thermal characteristics

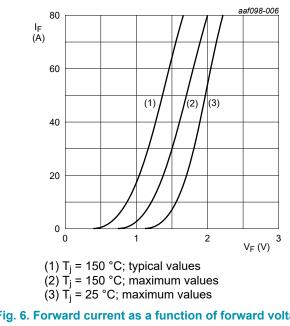
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-h)</sub>	thermal resistance from junction to heatsink	With heatsink compound; Fig. 5	-	2.3	2.6	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	35	-	K/W



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### 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.35	1.8	V
		I <sub>F</sub> = 30 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	0.96	-	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	500	μA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·				
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	37	65	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; T <sub>j</sub> = 25 °C; Fig. 7	-	85	-	ns
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	138	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/ \mu s; T_j = 25 ^{\circ}C$	-	11	-	А
		$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}$	-	18	-	А
Qr	recovered charge	$I_F = 30 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 25 \text{ °C}; Fig. 7$	-	461	-	nC
		I <sub>F</sub> = 30 A; V <sub>R</sub> = 200 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>i</sub> = 125 °C; <u>Fig. 7</u>	-	1227	-	nC



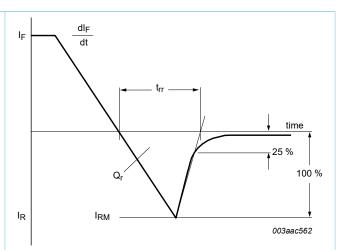
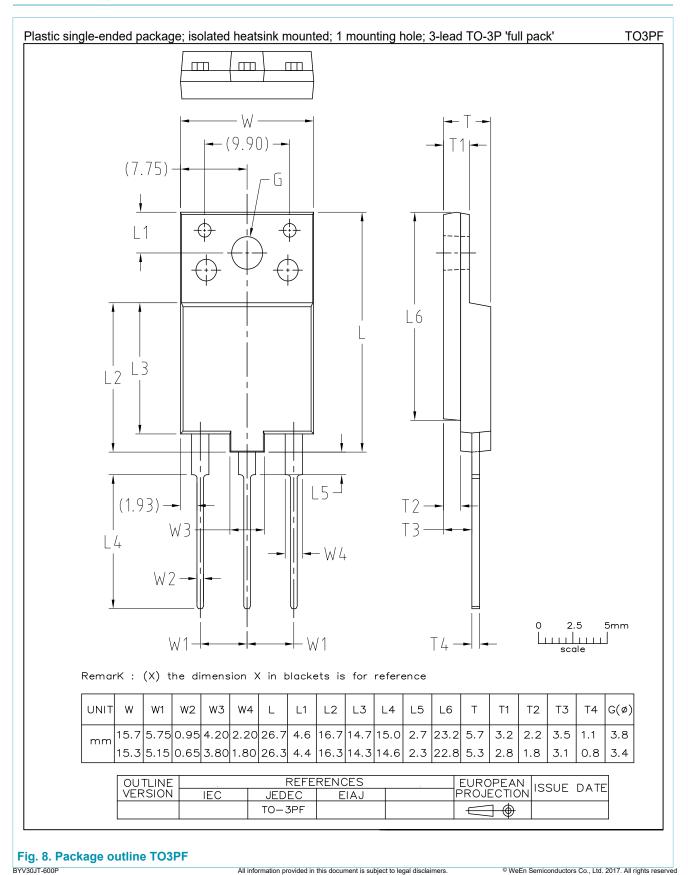




Fig. 6. Forward current as a function of forward voltage

**Ultrafast recovery diode** 

### 10. Package outline



#### **Ultrafast recovery diode**

## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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## **12. Contents**

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	5
9.	Characteristics	6
10	. Package outline	7
11.	. Legal information	8

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